REMARKS

The Office Action of March 1, 2004 was received and carefully reviewed. Reconsideration and withdrawal of the currently pending rejections are requested for the reasons advanced in detail below.

Initially, Applicants acknowledge with appreciation the courtesy extended by the Examiner during the Examiner's interview of April 14, 2004 to both the undersigned and Applicants' representatives from Japan.

Claims 1-13 are rejected under 35 U.S.C. 112 , first paragraph, as failing to comply with the written description requirement. This rejection is traversed for the reasons advanced in detail below.

Applicants contend that the presently pending claims include sufficient support by the specification to satisfy the requirements of Section 112, first paragraph, written description requirement. Support for all of the claim language is provided in the *Request for Interference Under 37 C.F.R. 1.607* filed on May 29, 2002. A copy of this claim chart is attached hereto. As can be seen from this chart, there is clearly adequate support for each any every claim limitation, particularly, for the features "a metal advanced lateral crystallization region" in claims 1-5 and 9-11; "a plurality of metal advanced crystallization regions" in claims 1 and 10; "a metal advanced crystallization region" in claims 6-7 and 9; "a metal induced lateral crystallization region" in claims 12-13 and "a plurality of metal induced crystallization regions" in claim 12, that are noted by the Examiner. Moreover, the specification is very detailed on how the regions are formed and what occurs in each region during formation.

The Examiner has failed to meet the burden of case law by not setting forth a specific, detailed reasoning for the rejection, i.e., pointing out where support is clearly filed. See, M.P.E.P. 2163.02 and 2163.04 which state:

> The courts have described the essential question to be addressed in a description requirement issue in a variety of ways. An objective standard for determining compliance with the written description requirement is, "does the description clearly allow persons of ordinary skill in the art to recognize that he or she invented what is claimed." *In re Gosteli*, 872 F.2d 1008, 1012, 10 USPQ2d 1614, 1618 (Fed. Cir. 1989). Under *Vas-Cath, Inc. v. Mahurkar*, 935 F.2d 1555, 1563-64, 19 USPQ2d 1111, 1117 (Fed. Cir. 1991), to satisfy the written description

requirement, an applicant must convey with reasonable clarity to those skilled in the art that, as of the filing date sought, he or she was in possession of the invention, and that the invention, in that context, is whatever is now claimed. The test for sufficiency of support in a parent application is whether the disclosure of the application relied upon "reasonably conveys to the artisan that the inventor had possession at that time of the later claimed subject matter." *Ralston Purina Co. v. Far-Mar-Co., Inc.*, 772 F.2d 1570, 1575, 227 USPQ 177, 179 (Fed. Cir. 1985) (quoting In re Kaslow, 707 F.2d 1366, 1375, 217 USPQ 1089, 1096 (Fed. Cir. 1983)).

The inquiry into whether the description requirement is met must be determined on a case-by-case basis and is a question of fact. *In re Wertheim*, 541 F.2d 257, 262, 191 USPQ 90, 96 (CCPA 1976). A description as filed is presumed to be adequate, unless or until sufficient evidence or reasoning to the contrary has been presented by the examiner to rebut the presumption. See, e.g., *In re Marzocchi*, 439 F.2d 220, 224, 169 USPQ 367, 370 (CCPA 1971). The examiner, therefore, must have a reasonable basis to challenge the adequacy of the written description. The examiner has the initial burden of presenting by a preponderance of evidence why a person skilled in the art would not recognize in an applicant's disclosure a description of the invention defined by the claims. *Wertheim*, 541 F.2d at 263, 191 USPQ at 97.

Moreover, the case law set forth in M.P.E.P. 2111.01 clearly allows the applicant to be his own lexicographer in drafting the claims.

Applicant may be his or her own lexicographer **>; however any special< meaning assigned to *>a< term ** "must be sufficiently clear in the specification that any departure from common usage would be so understood by a person of experience in the field of the invention." *Multiform Desiccants Inc. v. Medzam Ltd.*, 133 F.3d 1473, 1477, 45 USPQ2d 1429, 1432 (Fed. Cir. 1998). >See also *Process Control Corp. v. HydReclaim Corp.*, 190 F.3d 1350, 1357, 52 USPQ2d 1029, 1033 (Fed. Cir. 1999) and MPEP § 2173.05(a) <2100_2173_05_a.htm>.< as long as terminology is supported by the specification.

Further, the Federal Circuit in *Union Oil Co. of California v. Atlantic Richfield Co.*, 208 F3d 989, 54 USPQ2s 1227; (Fed. Cir. 2000) relies heavily on Wertheim and makes it clear that precise recitation of the claim limitation in disclosure is not requirement for "written description" to be satisfied, i.e., the invention does not have to be described ipsis verbis in order to satisfy the description requirement of 112. In view of the foregoing, it is believed that the rejection under Section 112, first paragraph, should be withdrawn.

Claim 4 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. Clearly, the specification provides support for this feature on page 7, lines 15-16, and in Figures 1B, 3B, 3C and 4C. The disclosure surrounding this features also provides the manner in which one of skill in the art can accomplish this feature, particularly when viewing Figures 3B and 3C. As a result, this rejection should likewise be overcome.

Claim 10 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. Support for these features are clearly provided in the attached claim chart. For the reasons advanced above with respect to claims 1-13, one of skill in the art would clearly have sufficient disclosure in the specification to permit formation of the recited transistor. Accordingly, it is respectfully requested that this rejection be reconsidered and withdrawn.

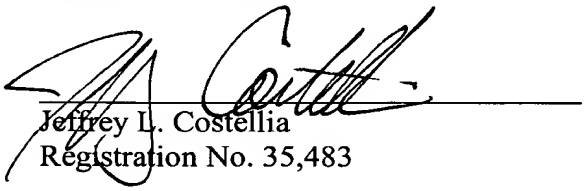
Claims 1-13 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

The Examiner feels the specification does not provide an adequate description of "a metal advanced lateral crystallization region" in claims 1-5 and 9-11; "a plurality of metal advanced crystallization regions" in claims 1 and 10; "a metal advanced crystallization region" in claims 6-7 and 9; "a metal induced lateral crystallization region" in claims 12-13 and "a plurality of metal induced crystallization regions" in claim 12, and, thus, the claims are indefinite. This rejection does not appear proper under second paragraph since these terms, in view of their descriptiveness, are definite on their face.

Even so, the support provided above and in the attached detailed claims chart clearly provides a description of each of the claimed features. Therefore, this rejection should likewise be overcome.

In view of the foregoing, it is respectfully requested that the rejections of record be reconsidered and withdrawn by the Examiner, that claims 1-13 be allowed and that the application be passed to issue. If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

Respectfully submitted,



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Claim Language	Support in Pending Application
1. A transistor comprising:	The present invention relates to a method of obtaining... (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a metal advanced lateral crystallization region	"forming regions containing at least one of nickel,... so that they adhere on part of the impurity regions, and by annealing the whole to crystallize it starting from the region containing nickel" (page 2, lines 8-11). "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17). "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).
formed on a substrate	substrate . . . 10 (page 6, line 11).
with a semiconductor material	title; "an amorphous silicon film" (page 6, line 12)
and including a channel region; and	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)
a plurality of metal advanced crystallization regions formed on sides of the metal advanced lateral crystallization region with a semiconductor material,	"[H]oles were created on the silicon oxide film 13 on the impurity regions to form nickel silicide (or nickel) films 17A and 17B . . . Then annealing was carried out . . to crystallize the impurity regions 16 and other semiconductor regions." (Fig. 1; page 7 lines 16-22).
wherein at least one boundary between the metal advanced lateral crystallization region and one of the metal advanced crystallization regions is located outside the channel region.	"[T]he present invention allows substantial elimination of the grain boundary between the source and drain and the active layer... by advancing the crystallization of the source and

	drain at the same time as crystallization of the active layer (channel forming region)." (page 2, lines 12-17); "According to the present invention,... the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18); "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b) and page 24, lines 3-5). See, also, Figure 1B showing nickel silicide films 17A and 17B only over a portion of the impurity regions 16A and 16B.
2. The transistor according to claim 1, wherein the metal advanced lateral crystallization region	Claim 1.
include (sic) impurity doped regions	[A]n impurity was introduced by a plasma doping method. . . . Impurity regions 16A and 16B were thus formed. (page 7, lines 10-15, Figure 1B).
formed on sides of the channel region.	"[H]oles were created on the silicon oxide film 13 on the impurity regions to form nickel silicide (or nickel) films 17A and 17B . . . Then annealing was carried out . . to crystallize the impurity regions 16 and other semiconductor regions." (Fig. 1; page 7 lines 16-22).
3. The transistor of claim 1, wherein the metal advanced lateral crystallization region	Claim 1.
includes source and drain regions.	"advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17.)
4. The transistor of claim 1, wherein the metal advanced lateral crystallization region includes no dopant portions formed on sides of the channel region.	"The impurity regions and the gate electrode were offset as seen in the figure." (page 7, lines 15-16; Figures 1B; 3B; 3C; 4C)
5. A transistor comprising:	The present invention relates to a method of obtaining... (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a channel region;	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)

a source region	"the source" (page 8, line 7).
having a first source portion adjacent to the channel region and a second source portion adjacent to the first source portion;	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the source portion and defines the first source portion and the second source portion.
and a drain region having a first drain portion adjacent to the channel region and a second drain portion adjacent to the first drain portion;	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the drain portion and defines the first drain portion and the second drain portion.
wherein the channel region and at least one of the first source portion and the first drain portion comprise a metal advanced lateral crystallization region.	"[T]heir direction of crystallization is the same. (page 8, lines 9-10) "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17.) "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was

	introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).
6. The transistor of claim 5, wherein the second source portion comprises a metal advanced crystallization region.	"[A]dvancing the crystallization of the source and drain" (page 2, line 15). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "[C]rystals are grown in the vertical direction with the surface of the substrate from the lower side of the semiconductor to the upper side thereof or vice versa." (page 24, lines 3-5).
7. The transistor of claim 5, wherein the second drain portion comprises a metal advanced crystallization region.	"[A]dvancing the crystallization of the source and drain" (page 2, line 15). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "[C]rystals are grown in the vertical direction with the surface of the substrate from the lower side of the semiconductor to the upper side thereof or vice versa." (page 24, lines 3-5).
8. The transistor of claim 5, wherein the source and drain regions are impurity doped.	[A]n impurity was introduced by a plasma doping method. . . . Impurity regions 16A and 16B were thus formed. (page 7, lines 10-15, Figure 1B).
9. The transistor of claim 5, wherein the channel region, the first source portion and the first drain portion comprise the metal advanced lateral crystallization region,	"advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17). "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he

	crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).
the second source region comprises a metal advanced crystallization region,	"[A]dvancing the crystallization of the source and drain" (page 2, line 15). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "[C]rystals are grown in the vertical direction with the surface of the substrate from the lower side of the semiconductor to the upper side thereof or vice versa." (page 24, lines 3-5).
and the second drain region comprises a metal advanced crystallization region.	"[A]dvancing the crystallization of the source and drain" (page 2, line 15). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "[C]rystals are grown in the vertical direction with the surface of the substrate from the lower side of the semiconductor to the upper side thereof or vice versa." (page 24, lines 3-5).
10. A transistor comprising:	The present invention relates to a method of obtaining... (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a metal advanced lateral crystallization region	"forming regions containing at least one of nickel,... so that they adhere on part of the impurity regions, and by annealing the whole to crystallize it starting from the region containing nickel" (page 2, lines 8-11). "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17). "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of

	crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).
formed on a substrate	substrate . . . 10 (page 6, line 11).
with a semiconductor material	title; "an amorphous silicon film" (page 6, line 12)
and including a channel region; and	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)
a plurality of metal advanced crystallization regions formed on sides of the metal advanced lateral crystallization region with a semiconductor material,	"[H]oles were created on the silicon oxide file 13 on the impurity regions to form nickel silicide (or nickel) films 17A and 17B . . . Then annealing was carried out . . to crystallize the impurity regions 16 and other semiconductor regions." (Fig. 1; page 7 lines 16-22).
wherein at least one portion between the metal advanced lateral crystallization region and one of the metal advanced crystallization regions is located outside the channel region.	"[T]he present invention allows substantial elimination of the grain boundary between the source and drain and the active layer... by advancing the crystallization of the source and drain at the same time as crystallization of the active layer (channel forming region)." (page 2, lines 12-17); "According to the present invention,... the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18); "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)).
11. A transistor comprising:	The present invention relates to a method of obtaining... (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a channel region;	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)
a source region	"the source" (page 8, line 7).
having a source portion adjacent to the channel region; and	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A

	and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the source portion and defines the first source portion and the second source portion.
a drain region having a drain portion adjacent to the channel region;	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the drain portion and defines the first drain portion and the second drain portion.
wherein the channel region and at least one of the source portion and the drain portion comprise a metal advanced lateral crystallization region.	"[T]heir direction of crystallization is the same. (page 8, lines 9-10) "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17.) "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24,

	lines 2-3).
12. A transistor comprising:	The present invention relates to a method of obtaining… (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a metal-induced lateral crystallization region	"forming regions containing at least one of nickel,… so that they adhere on part of the impurity regions, and by annealing the whole to crystallize it starting from the region containing nickel" (page 2, lines 8-11). "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17). "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).
formed on a substrate	substrate . . . 10 (page 6, line 11).
with a semiconductor material	title; "an amorphous silicon film" (page 6, line 12)
and including a channel region; and	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)
a plurality of metal-induced crystallization regions formed on sides of the metal induced lateral crystallization region with a semiconductor material,	"[H]oles were created on the silicon oxide film 13 on the impurity regions to form nickel silicide (or nickel) films 17A and 17B . . . Then annealing was carried out . . to crystallize the impurity regions 16 and other semiconductor regions." (Fig. 1; page 7 lines 16-22).
wherein at least one boundary between the metal induced lateral crystallization region and one of the metal induced crystallization regions is located outside the channel region.	"[T]he present invention allows substantial elimination of the grain boundary between the source and drain and the active layer… by advancing the crystallization of the source and

	drain at the same time as crystallization of the active layer (channel forming region)." (page 2, lines 12-17); "According to the present invention,... the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18); "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)).
13. A transistor comprising:	The present invention relates to a method of obtaining... (thin film transistor or TFT) (page 1, lines 5-8); The TFT . . .was fabricated through the process described above. (page 7, line 32 – page 8, line 1)
a channel region;	"channel forming region (the semiconductor region under the gate) electrode" (page 8, lines 8-9) (Fig. 1)
a source region	"the source" (page 8, line 7).
having a first source portion adjacent to the channel region and a second source portion adjacent to the first source portion; and	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the source portion and defines the first source portion and the second source portion.
a drain region having a first drain portion adjacent to the channel region and a second drain portion adjacent to the first drain portion;	"[A] film or the like containing a simple substance of nickel . . .is adhered to the impurity regions . . . and the region of the crystal silicon is expanded away therefrom as the starting point." (page 3, lines 13-18). As shown in Fig. 1B, the nickel silicide films 17A and 17B only cover the outer portion of the impurity regions 16A and 16B. "crystal growth advances from both ends of the island semiconductor region and finishes around the

	middle thereof. Accordingly, no grain boundary was produced in the channel forming region" (page 9, lines 15-19; Fig. 1 and 2(b)). Thus, any "grain boundary" exists in the drain portion and defines the first drain portion and the second drain portion.
wherein the channel region and at least one of the first source portion and the first drain portion comprise a metal induced lateral crystallization region.	"[T]heir direction of crystallization is the same. (page 8, lines 9-10) "advancing the crystallization of the source and drain at the same time as the crystallization of the active layer (channel forming region)." (page 2, lines 15-17.) "The crystal silicon which expands thus from a specific location has a structure close to a monocrystal having good continuous crystallinity." (page 3, lines 23-25). "[T]he crystal grew in the horizontal direction from the region into which nickel was introduced (the region contacting with an oxide film 51) to the region into which no nickel was introduced." (page 14, line 30 – page 15, line 1). "[C]rystal growth in the horizontal direction." (page 18, line 3). "[T]he present invention allows control of the direction of crystal growth." (page 18, lines 7-8). "[T]he crystals are grown in the transverse direction with the surface of the substrate" (page 24, lines 2-3).